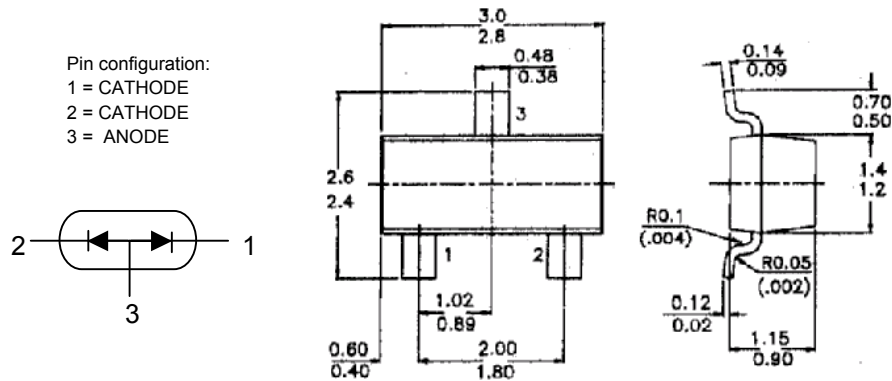


SILICON PLANAR VOLTAGE DUAL ZENER DIODE



SOT-23 Formed SMD Package
Package Outline Details. ALL DIMENSIONS IN mm

ABSOLUTE MAXIMUM RATINGS (per diode)

DESCRIPTION	SYMBOL	VALUE	UNIT
Working voltage	V_z	27	V
Working voltage tolerance		+/- 5	%
Total Power Dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	300	mW
Junction Temperature	T_j	150	$^\circ\text{C}$

RATINGS per diode (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Limiting values

Repetitive Peak Forward Current	I_{FRM}	250	mA
Repetitive Peak Working Current	I_{ZRM}	250	mA
Total Power Dissipation up to $T_{amb} = 25^\circ\text{C}^*$	P_{tot}	300	mW
Total Power Dissipation up to $T_{amb} = 25^\circ\text{C}^{**}$	P_{tot}	250	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Thermal Resistance

From Junction to ambient	$R_{th(j-a)}$	430	K/W
From Junction to ambient	$R_{th(j-a)}$	500	K/W

*Device mounted on a ceramic alumina.

**Device mounted on an FR5 circuit board.

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$ unless otherwise specified)

$$V_F = \max 0.9V @ 10mA$$

Device	working voltage		differential resistance		temperature coefficient		differential resistance		reverse current	
	$V_z(V)^{***}$ at $I_{z\text{ test}} = 2mA$		$r_{diff(ohm)}$ at $I_{z\text{ test}} = 2mA$		$S_z (mV/K)$ at $I_{z\text{ test}} = 2mA$		$r_{diff(ohm)}$ at $I_z = 0.5mA$		IR @ $T_a = 25^\circ\text{C}$	VR
	min	max	typ	max	min	max	typ	max	max	(V)
CZMA27	25.10	28.90	25	80	21.4	25.3	65	300	50	0.7

***Pulse test: 20ms</tp</50ms